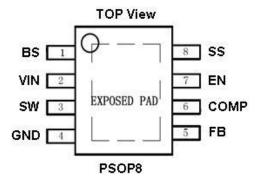


## **General Description**

The SE1484 is a monolithic synchronous buck regulator. The device integrates 95 m $\Omega$  MOSFETS that provide 3A continuous load current over a wide operating input voltage of 4.5V to 27V.Current mode control provides fast transient response and cycle-by-cycle current limit. An adjustable soft-start prevents inrush current at turn on.

## **Pin Configuration**



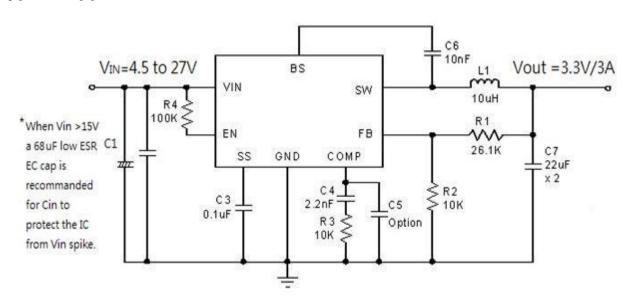
#### **Features**

- 3A Output Current
- Wide 4.5V to 27V Operating Input Range
- Output Adjustable from 0.925V to 0.8Vin
- Up to 93% Efficiency
- Programmable Soft-Start
- Stable with Low ESR Ceramic Output Capacitors
- Fixed 340KHZ Frequency
- Cycle-by-Cycle Over Current Protection
- Short Circuit Protection
- Input Under Voltage Lockout
- Package: PSOP-8

## **Applications**

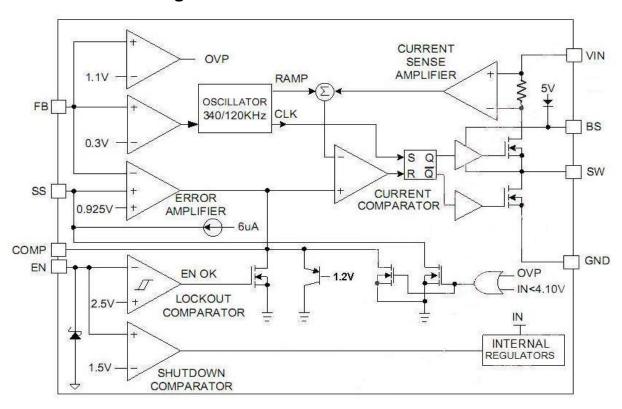
- Distributed Power Systems
- Green Electronics/ Appliances
- Notebook Computers
- Networking Systems
- FPGA, DSP, ASIC Power Supplies

# **Typical Application**





## **Functional Block Diagram**



## **Ordering Information**

Part Number	Part Number Marking Information		Remarks
SE1484-HF	SE1484	PSOP8 YYWW means Producti	
	YYWW-HF	F3UP6	XX=HF: Halogen Free.

**Absolute Maximum Rating** 

Parameter	Maximum	Units	
Input Supply Voltage	-0.3 to 30	V	
SW Voltage	-0.3 to V <sub>IN</sub> + 0.3	V	
BS Voltage	Vsw - 0.3 to Vsw + 6	V	
EN, FB, COMP Voltage	-0.3 to 5	V	
Continuous SW Current	Internally limited	А	
Junction to Ambient Thermal Resistance (θ <sub>JA</sub> )	20	°C/W	
Junction to Ambient Case Resistance (θ <sub>JC</sub> )	10	°C/W	
PSOP-8 Power Dissipation	Internal limit	W	
Maximum Junction Temperature	150	°C	
Storage Temperature Range	-65 to 150	°C	

Note: Exceeding these limits may damage the device. Even the duration of exceeding is very short.

Exposure to absolute maximum rating conditions for long periods may affect device reliability.



# **Recommended Operating Conditions**

Parameter	Symbol	Value	Units
Supply Input Voltage	V <sub>IN</sub>	4.5 to +27	V
Operating Junction Temperature	TJ	-20 to +125	°C

## **Electrical Characteristics**

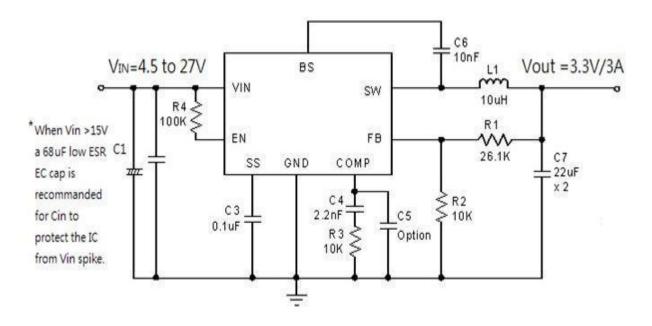
 $V_{IN} = 12V$ ;  $T_J = 25$ °C; unless otherwise specified

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Feedback Voltage	$V_{FB}$	4.5V ≤ V <sub>IN</sub> ≤ 27V	0.9	0.925	0.95	V
Feedback Overvoltage Threshold				1.1		V
High-Side Switch-On Resistance*				90		mΩ
Low-Side Switch-On Resistance*				70		mΩ
High-Side Switch Leakage		$V_{EN} = V_{SW} = 0V$	,	0.1	10	uA
Upper Switch Current Limit*		Min Duty Cycle	3.8	4.5		Α
Lower Switch Current Limit*		From Drain to Source		1.2		А
COMP to Current Limit Trans conductance	G <sub>COMP</sub>			5.2		A/V
Error Amplifier Trans conductance	$G_{EA}$	$\Delta I_{COMP} = \pm 10uA$		900		uA/V
Error Amplifier DC Gain*A	$V_{EA}$			400		V/V
Switching Frequency	f <sub>SW</sub>		300	340	380	KHz
Short Circuit Switching Frequency		$V_{FB} = 0V$		100		KHz
Minimum Duty Cycle	D <sub>MIN</sub>		7.5			%
Maximum Duty Cycle	D <sub>MAX</sub>			92		%
EN Shutdown Threshold Voltage		V <sub>EN</sub> Rising	1.1	1.4	2	V
EN Shutdown Threshold Voltage Hysteresis				180		mV
EN Lockout Threshold Voltage			2.2	2.5	2.7	V
EN Lockout Hysteresis				150		mV
Supply Current in Shutdown		V <sub>EN</sub> = 0V		0.3	3.0	uA
IC Supply Current in Operation		$V_{EN} = 3V$ , $V_{FB} = 1.0V$		1.3	1.5	mA
Input UVLO Threshold Rising	UVLO	V <sub>EN</sub> Rising	3.8	4.0	4.4	V
Input UVLO Threshold Hysteresis				150		mV
Soft-start Current		V <sub>SS</sub> = 0V		6		uA
Soft-start Period		C <sub>SS</sub> =0.1uF		15		mS
Thermal Shutdown Temperature*		Hysteresis =25°C		155		$^{\circ}\mathbb{C}$

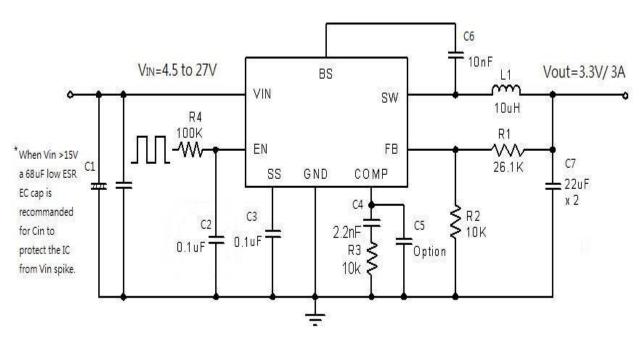
Note: \* Guaranteed by design, not tested



# **Typical Application**



SE1484 Circuit, 3.3V/3A output



SE1484 Circuit, 3.3V/3A output with EN function Note: C2 is required for separate EN signal.



## 3A 27V Synchronous Buck Converter

## **Applications**

## **Output Voltage Setting**

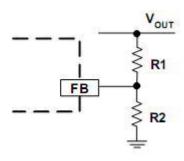


Figure 1. Output Voltage Setting

Figure 1 shows the connections for setting the output voltage. Select the proper ratio of the two feedback resistors R1 and R2 based on the output voltage. Typically, use R2 $\approx$ 10K $\Omega$  and determine R1 from the following equation:

$$R1 = R2 \left( \frac{V_{OUT}}{0.925 \text{V}} - 1 \right) \tag{1}$$

Table1—Recommended Resistance Values:

VOUT	R1	R2
1V	1.0ΚΩ	12ΚΩ
1.2V	3.0ΚΩ	10ΚΩ
1.8V	9.53ΚΩ	10ΚΩ
2.5V	16.9ΚΩ	10ΚΩ
3.3V	26.1ΚΩ	10ΚΩ
5V	44.2ΚΩ	10ΚΩ
12V	121ΚΩ	10ΚΩ

#### Inductor Selection

The inductor maintains a continuous current to the output load. This inductor current has a ripple that is dependent on the inductance value: higher inductance reduces the peak-to-peak ripple current. The trade off for high inductance value is the increase in inductor core size and series resistance, and the reduction in current handling capability. In general, select an

inductance value.

L based on the ripple current requirement:

$$L = \frac{V_{OUT} \cdot (V_{IN} - V_{OUT})}{V_{IN} f_{SW} I_{OUTMAX} K_{RIPPLE}}$$
 (2)

Where  $V_{IN}$  is the input voltage, VOUT is the output voltage,  $f_{SW}$  is the switching frequency, IOUTMAX is the maximum output current, and KRIPPLE is the ripple factor. Typically, choose  $K_{RIPPLE} = ~30\%$  to correspond to the peak-to-peak ripple current being ~30% of the maximum output current.

With this inductor value, the peak inductor current is  $I_{OUT}$ •(1+ $K_{RIPPLE}$ /2). Make sure that this peak inductor current is less than the upper switch current limit. Finally, select the inductor core size so that it does not saturate at the current limit. Typical inductor values for various output voltages are shown in Table 2.

Table 2. Typical Inductor Values

V <sub>OUT</sub>	1V	1.2V	1.8V	2.5V	3.3V	5V	9V
L(uH)	4.7	4.7	10	10	10	10	22

### **Input Capacitor**

The input capacitor needs to be carefully selected to maintain sufficiently low ripple at the supply input of the converter. A low ESR Electrolytic (EC) capacitor is highly recommended. Since large current flows in and out of this capacitor during switching, its ESR also affects efficiency. When EC cap is used, the input capacitance needs to be equal to or higher than 68uF. The RMS ripple current rating needs to be higher than 50% of the output current. The input capacitor should be placed close to the VIN and GND pins of the IC, with the shortest traces possible. The input capacitor can be placed a little bit away if a small parallel 0.1uF ceramic capacitor is placed right next to the IC.

When Vin is >15V, pure ceramic Cin (\* no EC cap) is not recommended. This is because the ESR of a ceramic cap is often too small, Pure ceramic Cin will work



## 3A 27V Synchronous Buck Converter

with the parasite inductance of the input trace and forms a Vin resonant tank. When Vin is hot plug in/out, this resonant tank will boost the Vin spike to a very high voltage and damage the IC.

#### **Output Capacitor**

The output capacitor also needs to have low ESR to keep low output voltage ripple. In the case of ceramic output capacitors,  $R_{\rm ESR}$  is very small and does not contribute to the ripple. Therefore, a lower capacitance value can be used for ceramic capacitors. In the case of tantalum or electrolytic capacitors, the ripple is dominated by  $R_{\rm ESR}$  multiplied by the ripple current. In that case, the output capacitor is chosen to have sufficiently low ESR.

For ceramic output capacitors, typically choose of about 22uF. For tantalum or electrolytic capacitors, choose a capacitor with less than  $50m\Omega$  ESR.

#### **Optional Schottky Diode**

During the transition between high-side switch and low-side switch, the body diode of the low side power MOSFET conducts the inductor current. The forward voltage of this body diode is high. An optional Schottky diode may be paralleled between the SW pin and GND pin to improve overall efficiency.

#### **Stability Compensation**

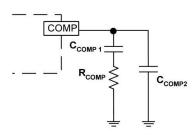


Figure 2. Stability Compensation

 $C_{\text{COMP2}}$  is needed only for high ESR output capacitor.

The feedback loop of the IC is stabilized by the components at the COMP pin, as shown in Figure

2. The DC loop gain of the system is determined by the following equation:

$$A_{VDC} = \frac{0.925 \, V}{I_{OUT}} A_{VEA} \, G_{COMP} \tag{4}$$

The dominant pole P1 is due to C<sub>COMP</sub>1:

$$f_{P1} = \frac{G_{EA}}{2\pi A_{VEA} C_{COMP1}}$$
 (5)

The second pole P2 is the output pole:

$$f_{P2} = \frac{I_{OUT}}{2\pi V_{OUT} C_{OUT}}$$
 (6)

The first zero Z1 is due to  $R_{COMP}$  and  $C_{COMP}$ :

$$f_{Z1} = \frac{1}{2\pi R_{COMP} C_{COMP1}} \tag{7}$$

And finally, the third pole is due to  $R_{COMP}$  and  $C_{COMP2}$  (if  $C_{COMP2}$  is used):

$$f_{P3} = \frac{1}{2\pi R_{COMP} C_{COMP2}} \tag{8}$$

The following steps should be used to compensate the IC:

STEP1. Set the crossover frequency at 1/10 of the switching frequency via  $R_{\text{COMP}}$ :

$$R_{COMP} = \frac{2\pi V_{OUT} C_{OUT} f_{SW}}{10G_{EA} G_{COMP} \bullet 0.925V}$$
 (9)

but limit  $R_{COMP}$  to  $10K\Omega$  maximum. More than 10  $K\Omega$  is easy to cause overshoot at power on.

STEP2. Set the zero  $f_{Z1}$  at 1/4 of the crossover frequency. If  $R_{COMP}$  is less than  $10K\Omega$ , the equation for  $C_{COMP}$  is:

$$C_{COMP1} = \frac{0.637}{R_{COMP} \times fc} (F) \qquad (10)$$



# STEP3. If the output capacitor's ESR is high enough to cause a zero at lower than 4 times the crossover frequency, an additional compensation capacitor $C_{\text{COMP2}}$ is required. The condition for using $C_{\text{COMP2}}$ is:

$$\pi \times C_{OUT} \times R_{ESR} \times fs \ge 1$$
 (11)

And the proper value for  $C_{\text{COMP2}}$  is:

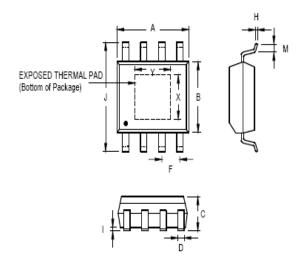
$$C_{COMP2} = \frac{C_{OUT}R_{ESRCOUT}}{R_{COMP}}$$
 (12)

Though  $C_{\text{COMP2}}$  is unnecessary when the output capacitor has sufficiently low ESR, a small value  $C_{\text{COMP2}}$  such as 100pF may improve stability against PCB layout parasitic effects

Table 4 - Component Selection Guide for Stability Compensation

Vin Range	Vout	Cout	Rcomp	Ccomp	Ccomp2	Inductor
(V)	(V)	Cout	$(R3)(k\Omega)$	(C4)(nF)	(C5)(pF)	(uH)
5 – 12	1.0		3.3	5.6	none	4.7
5 – 15	1.2	1	3.9	4.7	none	4.7
5 – 15	1.8	22uFx2	5.6	3.3	none	10
5 – 15	2.5	] _ [	8.2	2.2	none	10
5 – 15	3.3	Ceramic	10	2	none	10
5 – 15	5	1 [	10	3.3	none	10
5 – 12	1.0					4.7
5 – 15	1.2	1				4.7
5 – 23	1.8	470uF/	10	6.8	680	
5 – 27	2.5	6.3V/120mΩ				
5 – 27	3.3	1				10
5 – 27	5	1				

# **Outline Drawing For PSOP8**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	4.801	5.004	0.189	0.197	
В	3.810	3.988	0.150	0.157	
С	1.346	1.753	0.053	0.069	
D	0.330	0.508	0.013	0.020	
F	1.194	1.346	0.047	0.053	
Н	0.191	0.254	0.008	0.010	
_	0.000	0.152	0.000	0.006	
J	5.791	6.198	0.228	0.244	
М	0.406	1.270	0.016	0.050	
Х	2.057	2.515	0.081	0.099	
Υ	2.057	3.404	0.081	0.134	



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